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Tech ID: 19316

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

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- ▶ [Defect Reduction in GaN films using in-situ SiNx Nanomask](#)
- ▶ [A Structure For Increasing Mobility In A High-Electron-Mobility Transistor](#)
- ▶ [Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices](#)
- ▶ [Methods for Locally Changing the Electric Field Distribution in Electron Devices](#)
- ▶ [Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices](#)
- ▶ [\(In,Ga,Al\)N Optoelectronic Devices with Thicker Active Layers for Improved Performance](#)
- ▶ [GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors](#)
- ▶ [Novel Current-Blocking Layer in High-Power Current Aperture Vertical Electron Transistors \(CAVETs\)](#)
- ▶ [III-N Transistor With Stepped Cap Layers](#)
- ▶ [III-N Based Material Structures and Circuit Modules Based on Strain Management](#)

